METHOD OF PRODUCING SIMOX WAFER

ABSTRACT

A SIMOX wafer is produced by implanting an oxygen ions into a surface of a Si substrate and then conducting a high-temperature annealing, in which an atmosphere in at least an end stage of the high-temperature annealing treatment is an Ar or N_2 atmosphere containing an oxygen of more than 3 volume% but not more than 10 volume %.

Fig. 1